

MOS INTEGRATED CIRCUIT μ PD431000A-X

1M-BIT CMOS STATIC RAM 128K-WORD BY 8-BIT EXTENDED TEMPERATURE OPERATION

Description

The μPD431000A-X is a high speed, low power, and 1,048,576 bits (131,072 words by 8 bits) CMOS static RAM.

The μ PD431000A-X has two chip enable pins (/CE1, CE2) to extend the capacity. And battery backup is available. In addition to this, A and B versions are low voltage operations.

The μ PD431000A-X is packed in 32-pin PLASTIC SOP, 32-pin PLASTIC TSOP (I) (8 × 13.4 mm) and (8 × 20 mm).

Features

- 131,072 words by 8 bits organization
- Fast access time: 70, 85, 100, 120, 150 ns (MAX.)
- Low voltage operation (A version: Vcc = 3.0 to 5.5 V, B version: Vcc = 2.7 to 5.5 V)
- Operating ambient temperature: $T_A = -25$ to +85 °C
- Low Vcc data retention: 2.0 V (MIN.)
- Output Enable input for easy application
- Two Chip Enable inputs: /CE1, CE2

Part number	Access time	Operating supply	Operating ambient		Supply curre	ent
	ns (MAX.)	voltage	temperature	At operating	At standby	At data retention
		V	°C	mA (MAX.)	μΑ (MAX.)	μΑ (MAX.) Note1
μPD431000A-xxX	70, 85	4.5 to 5.5	–25 to +85	70	50	2.5
μPD431000A-AxxX	70 ^{Note2} , 100	3.0 to 5.5		35 Note3	26 Note5	
μPD431000A-BxxX	70 Note2, 100, 120, 150	2.7 to 5.5		30 Note4	22 Note6	

Notes 1. TA \leq 40 °C

- **2.** Vcc = 4.5 to 5.5 V
- 3. 70 mA (Vcc > 3.6 V)
- 4. 70 mA (Vcc > 3.3 V)
- **5.** 50 μ A (Vcc > 3.6 V)
- **6.** 50 μ A (Vcc > 3.3 V)

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Ordering Information

Part number	Package	Access time	Operating supply	Operating ambient	Remark
		ns (MAX.)	voltage	temperature	
			V	°C	
μPD431000AGW-70X	32-pin PLASTIC SOP	70	4.5 to 5.5	-25 to +85	-
	(13.34 mm (525))				
μPD431000AGZ-70X-KJH	32-pin PLASTIC TSOP (I)				
μPD431000AGZ-85X-KJH	(8 × 20) (Normal bent)	85			
μPD431000AGZ-A10X-KJH		100	3.0 to 5.5		A version
μPD431000AGZ-B10X-KJH		100	2.7 to 5.5		B version
μPD431000AGZ-B12X-KJH		120			
μPD431000AGZ-B15X-KJH		150			
μPD431000AGZ-70X-KKH	32-pin PLASTIC TSOP (I)	70	4.5 to 5.5		_
μPD431000AGZ-85X-KKH	(8 × 20) (Reverse bent)	85			
μPD431000AGZ-A10X-KKH		100	3.0 to 5.5		A version
μPD431000AGU-B10X-9JH	32-pin PLASTIC TSOP (I)	100	2.7 to 5.5		B version
μPD431000AGU-B12X-9JH	(8×13.4) (Normal bent)	120			
μPD431000AGU-B15X-9JH		150			
μPD431000AGU-B12X-9KH	32-pin PLASTIC TSOP (I)	120	2.7 to 5.5		
μPD431000AGU-B15X-9KH	(8 × 13.4) (Reverse bent)	150			
μPD431000AGW-70X-A	32-pin PLASTIC SOP	70	4.5 to 5.5		-
	(13.34 mm (525))				
μPD431000AGZ-70X-KJH-A	32-pin PLASTIC TSOP (I)				
μPD431000AGZ-85X-KJH-A	(8 × 20) (Normal bent)	85			
μPD431000AGZ-A10X-KJH-A		100	3.0 to 5.5		A version
μPD431000AGZ-B10X-KJH-A		100	2.7 to 5.5		B version
μPD431000AGZ-B12X-KJH-A		120			
μPD431000AGZ-B15X-KJH-A		150			
μPD431000AGZ-70X-KKH-A	32-pin PLASTIC TSOP (I)	70	4.5 to 5.5		_
μPD431000AGZ-85X-KKH-A	(8 × 20) (Reverse bent)	85			
μPD431000AGZ-A10X-KKH-A		100	3.0 to 5.5		A version
μPD431000AGU-B10X-9JH-A	32-pin PLASTIC TSOP (I)	100	2.7 to 5.5		B version
μPD431000AGU-B12X-9JH-A	(8 × 13.4) (Normal bent)	120			
μPD431000AGU-B15X-9JH-A		150			
μPD431000AGU-B12X-9KH-A	32-pin PLASTIC TSOP (I)	120	2.7 to 5.5		
μPD431000AGU-B15X-9KH-A	(8 × 13.4) (Reverse bent)	150			

<R> Remark Products with -A at the end of the part number are lead-free products.

<R>



Pin Configurations (Marking Side)

/xxx indicates active low signal.

32-pin PLASTIC SOP (13.34 mm (525)) $[\mu PD431000AGW-xxX] \\ [\mu PD431000AGW-xxX-A]$

NC O - Vcc 32 A16 O 2 31 **○** A15 3 A14 O 30 → CE2 A12 O -○ /WE 29 A7 O 5 28 A6 O 6 -○ A8 27 A5 O **⊖** A9 26 A4 🔾 25 - O A11 A3 ()-9 24 -() /OE 10 A2 🔾 23 -○ A10 11 22 -() /CE1 A1 🔾 12 A0 🔾 21 **-**○ I/O8 I/O1 ○- 13 20 **-**○ I/O7 1/02 ○◄ 14 19 **-**○ I/O6 I/O3 ○- 15 18 **→**○ I/O5 GND O 16 17 -○ I/O4

A0 - A16 : Address inputs
I/O1 - I/O8 : Data inputs / outputs

/CE1, CE2 : Chip Enable 1, 2 /WE : Write Enable

/OE : Output Enable
Vcc : Power supply

GND : Ground

NC : No connection

Remark Refer to **Package Drawings** for the 1-pin index mark

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32-pin PLASTIC TSOP (I) (8×20) (Normal bent)

[μ PD431000AGZ-xxX-KJH]

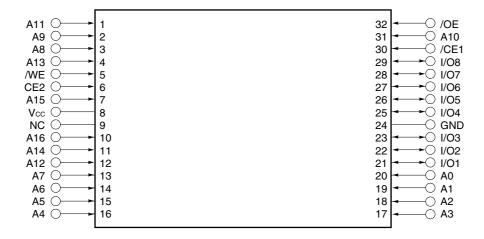
[μ PD431000AGZ-AxxX-KJH]

[μ PD431000AGZ-BxxX-KJH]

[μ PD431000AGZ-xxX-KJH-A]

[μ PD431000AGZ-AxxX-KJH-A]

[μ PD431000AGZ-BxxX-KJH-A]



32-pin PLASTIC TSOP (I) (8×20) (Reverse bent)

[µPD431000AGZ-xxX-KKH]

[μ PD431000AGZ-AxxX-KKH]

[μ PD431000AGZ-xxX-KKH-A]

[μ PD431000AGZ-AxxX-KKH-A]

		7
/OE ○	32 1	← ○ A11
A10 ○ →	31 2	← ○ A9
/CE1 ○ →	30 3	← ○ A8
I/O8 ○ < →	29 4	←
1/07 ○	28 5	← ∴ /WE
I/O6 ○ < →	27 6	CE2
I/O5 ○ < →	26 7	→ ○ A15
1/04 ○≺ →	25 8	── Vcc
GND O	24 9	——○ NC
I/O3 ○ < →	23 10	←
I/O2 ○ < →	22 11	←
I/O1 ○ < →	21 12	← ○ A12
A0 ○ →	20 13	← ○ A7
A1 ○ →	19 14	←
A2 ○ →	18 15	- ○ A5
A3 ○ →	17 16	←
		1

A0 - A16 : Address inputs /OE : Output Enable I/O1 - I/O8: Data inputs / outputs /CE1, CE2: Chip Enable 1, 2 GND: Ground

/WE : Write Enable NC : No connection

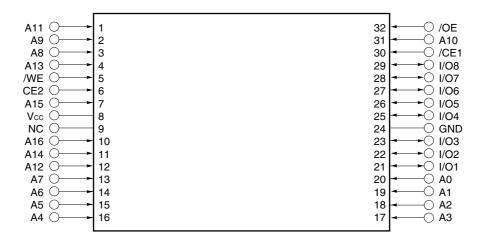
Remark Refer to Package Drawings for the 1-pin index mark.

32-pin PLASTIC TSOP (I) (8×13.4) (Normal bent)

[μPD431000AGU-BxxX-9JH] [μPD431000AGU-BxxX-9JH-A]

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32-pin PLASTIC TSOP (I) (8×13.4) (Reverse bent) $[\mu PD431000AGU-BxxX-9KH] \\ [\mu PD431000AGU-BxxX-9KH-A]$

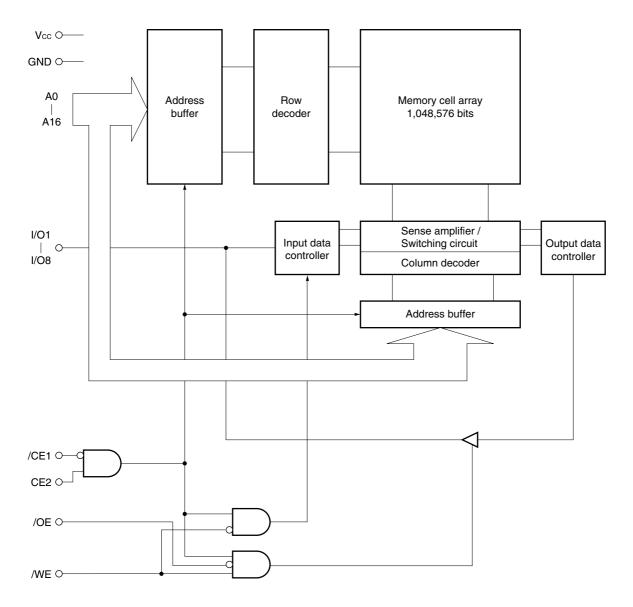
/OE 〇 32 1 A10 (**○ A9** 31 2 /CE1 C 30 3 O A8 I/O8 () 29 4 **○ A13** I/07 O-5 · /WE 28 1/06 ○ 27 6 ○ CE2 I/O5 🔿 26 7 I/O4 (8 25 GND (24 9 ○ NC I/O3 🔾 23 10 ○ A16 I/O2 () 22 11 ○ A14 I/O1 () **○ A12** 21 12 A0 (20 13 ○ A7 **A1** ○ 19 14 A2 🔿 **○ A5** 18 15 A3 🔾 17 16

> A0 - A16 : Address inputs I/O1 - I/O8 : Data inputs / outputs /CE1, CE2 : Chip Enable 1, 2 /WE : Write Enable /OE : Output Enable VccPower supply **GND** Ground NC : No connection

Remark Refer to Package Drawings for the 1-pin index mark.



Block Diagram



Truth Table

/CE1	CE2	/OE	/WE	Mode	I/O	Supply current
Н	×	×	×	Not selected	High impedance	IsB
×	L	×	×			
L	Н	Н	Н	Output disable		Icca
L	Н	L	Н	Read	D оит	
L	Н	×	L	Write	Din	

 $\textbf{Remark} \quad \times \, : \, V_{IH} \,\, or \,\, V_{IL}$



Electrical Specifications

Absolute Maximum Ratings

Parameter	Symbol	Condition	Rating	
Supply voltage	Vcc		-0.5 ^{Note} to +7.0	V
Input / Output voltage	VT		-0.5 Note to Vcc + 0.5	V
Operating ambient temperature	TA		–25 to +85	°C
Storage temperature	T _{stg}		-55 to +125	°C

Note -3.0 V (MIN.) (Pulse width: 30 ns)

Caution Exposing the device to stress above those listed in Absolute Maximum Rating could cause permanent damage. The device is not meant to be operated under conditions outside the limits described in the operational section of this specification. Exposure to Absolute Maximum Rating conditions for extended periods may affect device reliability.

Recommended Operating Conditions

Parameter	Symbol	Condition	μPD431000A-xxX		μPD431000A-AxxX		μPD4310	Unit	
			MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
Supply voltage	Vcc		4.5	5.5	3.0	5.5	2.7	5.5	V
High level input voltage	VIH		2.4	Vcc+0.5	2.4	Vcc+0.5	2.4	Vcc+0.5	V
Low level input voltage	VIL		-0.3 Note	+0.6	-0.3 Note	+0.5	-0.3 Note	+0.5	V
Operating ambient temperature	Ta		-25	+85	-25	+85	-25	+85	°C

Note -3.0 V (MIN.) (Pulse width: 30 ns)

Capacitance (T_A = 25 °C, f = 1 MHz)

Parameter	Symbol	Test conditions	MIN.	TYP.	MAX.	Unit
Input capacitance	Cin	V _{IN} = 0 V			6	pF
Input / Output capacitance	C _{I/O}	V _{I/O} = 0 V			10	pF

Remarks 1. VIN: Input voltage

Vi/o: Input / Output voltage

2. These parameters are not 100% tested.

Data Sheet M10430EJAV0DS 7



DC Characteristics (Recommended Operating Conditions Unless Otherwise Noted)

Parameter	Symbol	Test condit	ion	μPD4	431000/	۹-xxX	μPD4	31000 <i>A</i>	-AxxX	μPD4	31000 <i>A</i>	\-BxxX	Unit
				MIN.	TYP.	MAX.	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.	
Input leakage current	lu	V _{IN} = 0 V to V _{CC}		-1.0		+1.0	-1.0		+1.0	-1.0		+1.0	μΑ
I/O leakage	ILO	V _{VO} = 0 V to V _{CC} ,		-1.0		+1.0	-1.0		+1.0	-1.0		+1.0	μА
current		/CE1 = V _{IH} or CE2 = V	VIL										
		or /WE = V _{IL} or /OE =	· V _{IH}										
Operating	ICCA1	/CE1 = V _{IL} , CE2 = V _I	١,		40	70		40	70		40	70	mA
supply current		I _{I/O} = 0 mA	Vcc ≤ 3.6 V		_	_		15	35		_	_	
		Minimum cycle time	Vcc ≤ 3.3 V			_			_		15	30	
	Icca2	/CE1 = V _{IL} , CE2 = V _I	١,			15			15			15	
		I _{I/O} = 0 mA,	Vcc ≤ 3.6 V			_			10			_	
		Cycle time = ∞	Vcc ≤ 3.3 V			_			_			8	
	Іссаз	/CE1 ≤ 0.2 V, CE2 ≥ Vcc – 0.2 V,				10			10			10	
		Cycle time = 1 μ s, I	o = 0 mA,										
		$V_{IL} \leq 0.2 V$,	Vcc ≤ 3.6 V			_			8			-	
		$V_{IH} \ge V_{CC} - 0.2 V$	Vcc ≤ 3.3 V			_			_			7	
Standby	Isa	/CE1 = V _{IH} or CE2 = V	VIL			3			3			3	mA
supply current			Vcc ≤ 3.6 V			-			2			_	
			Vcc ≤ 3.3 V			_			_			2	
	I _{SB1}	/CE1 ≥ Vcc - 0.2 V,			1	50		_	50		_	50	μА
		CE2 ≥ Vcc - 0.2 V	Vcc ≤ 3.6 V		_	_		0.5	26		_	_	
			Vcc ≤ 3.3 V		_	_		_	_		0.5	22	
	I _{SB2}	CE2 ≤ 0.2 V			1	50		_	50		_	50	
			Vcc ≤ 3.6 V		_	_		0.5	26		_	_	
			Vcc ≤ 3.3 V		_	-		_	_		0.5	22	
High level	Vон	Iон = −1.0 mA, Vcc ≥ 4.5 V		2.4			2.4			2.4			V
output voltage		Iон = -0.5 mA		_			2.4			2.4			
Low level	Vol	I _{OL} = 2.1 mA, V _{CC} ≥ 4	.5 V			0.4			0.4			0.4	V
output voltage		I _{OL} = 1.0 mA				_			0.4			0.4	

Remarks 1. VIN: Input voltage

Vi/o : Input / Output voltage

2. These DC characteristics are in common regardless product classification.

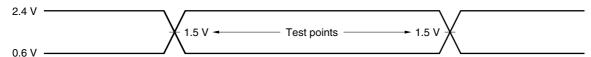


AC Characteristics (Recommended Operating Conditions Unless Otherwise Noted)

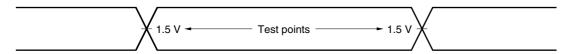
AC Test Conditions

[μ PD431000A-70X, μ PD431000A-85X]

Input Waveform (Rise and Fall Time ≤ 5 ns)

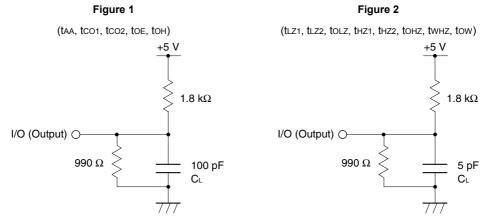


Output Waveform



Output Load

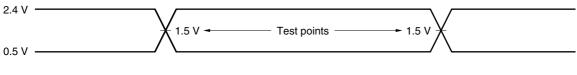
AC characteristics should be measured with the following output load conditions.



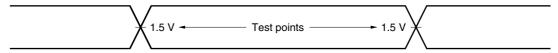
Remark CL includes capacitance of the probe and jig, and stray capacitance.

[μ PD431000A-A10X, μ PD431000A-B10X, μ PD431000A-B12X, μ PD431000A-B15X]

Input Waveform (Rise and Fall Time ≤ 5 ns)



Output Waveform



Output Load

AC characteristics should be measured with the following output load conditions.

Part number	Output load condition					
	taa, tco1, tco2, toe, toh	tlz1, tlz2, tolz, thz1, thz2, tohz, twhz, tow				
μPD431000A-A10X, μPD431000A-B10X, μPD431000A-B12X	1TTL + 50 pF	1TTL + 5 pF				
μPD431000A-B15X	1TTL + 100 pF	1TTL + 5 pF				



Read Cycle (1/2)

Parameter	Symbol		Vcc≥	4.5 V		Vcc≥	3.0 V	Unit	Condition
		μPD4310	μPD431000A-70X		μPD431000A-85X		00A-A10X		
		μPD4310	00A-AxxX						
		μPD4310	00A-BxxX						
		MIN.	MAX.	MIN.	MAX.	MIN.	MAX.		
Read cycle time	t RC	70		85		100		ns	
Address access time	taa		70		85		100	ns	Note
/CE1 access time	t co1		70		85		100	ns	
CE2 access time	tc02		70		85		100	ns	
/OE to output valid	t oe		35		45		50	ns	
Output hold from address change	tон	10		10		10		ns	
/CE1 to output in low impedance	t LZ1	10		10		10		ns	
CE2 to output in low impedance	t LZ2	10		10		10		ns	
/OE to output in low impedance	tolz	5		5		5		ns	
/CE1 to output in high impedance	t _{HZ1}		25		30		35	ns	
CE2 to output in high impedance	t _{HZ2}		25		30		35	ns	
/OE to output in high impedance	tонz		25		30		35	ns	

Note See the output load.

Remark These AC characteristics are in common regardless of package types.

Read Cycle (2/2)

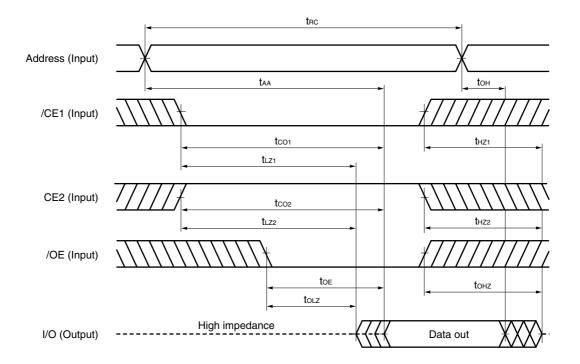
Parameter	Symbol			Vcc≥	2.7 V		Unit	Condition	
		μPD4310	00A-B10X	μPD4310	00A-B12X	μPD4310	00A-B15X		
		MIN.	MAX.	MIN.	MAX.	MIN.	MAX.		
Read cycle time	t RC	100		120		150		ns	
Address access time	taa		100		120		150	ns	Note
/CE1 access time	t co1		100		120		150	ns	
CE2 access time	t co2		100		120		150	ns	
/OE to output valid	toe		50		60		70	ns	
Output hold from address change	tон	10		10		10		ns	
/CE1 to output in low impedance	t LZ1	10		10		10		ns	
CE2 to output in low impedance	t LZ2	10		10		10		ns	
/OE to output in low impedance	tolz	5		5		5		ns	
/CE1 to output in high impedance	t _{HZ1}		35		40		50	ns	
CE2 to output in high impedance	t _{HZ2}		35		40		50	ns	
/OE to output in high impedance	tонz		35		40		50	ns	

Note See the output load.

Remark These AC characteristics are in common regardless of package types.



Read Cycle Timing Chart



Remark In read cycle, /WE should be fixed to high level.



Write Cycle (1/2)

Parameter	Symbol		Vcc≥	4.5 V		Vcc≥	3.0 V	Unit	Condition
		μPD4310	μPD431000A-70X		μPD431000A-85X		μPD431000A-A10X		
		μPD4310	μPD431000A-AxxX						
		μPD4310	00A-BxxX						
		MIN.	MAX.	MIN.	MAX.	MIN.	MAX.		
Write cycle time	twc	70		85		100		ns	
/CE1 to end of write	tcw1	55		70		80		ns	
CE2 to end of write	tcw2	55		70		80		ns	
Address valid to end of write	taw	55		70		80		ns	
Address setup time	t AS	0		0		0		ns	
Write pulse width	t wp	50		60		60		ns	
Write recovery time	twr	5		5		0		ns	
Data valid to end of write	t _{DW}	35		35		60		ns	
Data hold time	tон	0		0		0		ns	
/WE to output in high impedance	t wHz		25		30		35	ns	Note
Output active from end of write	tow	5		5		5		ns	

Note See the output load.

Remark These AC characteristics are in common regardless of package types.

Write Cycle (2/2)

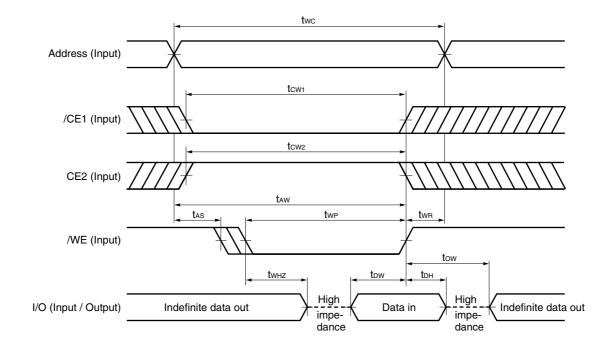
Parameter	Parameter Symbol Vcc ≥ 2.7			Unit	Condition				
		μPD4310	μPD431000A-B10X μPD431000A-B12X		μPD431000A-B15X				
		MIN.	MAX.	MIN.	MAX.	MIN.	MAX.		
Write cycle time	twc	100		120		150		ns	
/CE1 to end of write	tcw1	80		100		120		ns	
CE2 to end of write	tcw2	80		100		120		ns	
Address valid to end of write	taw	80		100		120		ns	
Address setup time	tas	0		0		0		ns	
Write pulse width	twp	60		85		100		ns	
Write recovery time	twr	0		0		0		ns	
Data valid to end of write	tow	60		60		80		ns	
Data hold time	tон	0		0		0		ns	
/WE to output in high impedance	t wHz		35		40		50	ns	Note
Output active from end of write	tow	5		5		5		ns	

Note See the output load.

Remark These AC characteristics are in common regardless of package types.



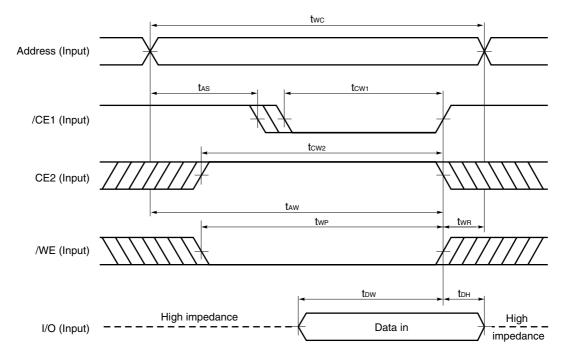
Write Cycle Timing Chart 1 (/WE Controlled)



- Cautions 1. During address transition, at least one of pins /CE1, CE2, /WE should be inactivated.
 - 2. Do not input data to the I/O pins while they are in the output state.
- Remarks 1. Write operation is done during the overlap time of a low level /CE1, /WE and a high level CE2.
 - 2. If /CE1 changes to low level at the same time or after the change of /WE to low level, or if CE2 changes to high level at the same time or after the change of /WE to low level, the I/O pins will remain high impedance state.
 - 3. When /WE is at low level, the I/O pins are always high impedance. When /WE is at high level, read operation is executed. Therefore /OE should be at high level to make the I/O pins high impedance.

Data Sheet M10430EJAV0DS 13

Write Cycle Timing Chart 2 (/CE1 Controlled)

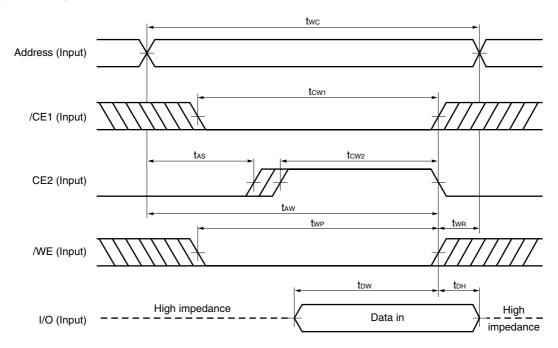


Cautions 1. During address transition, at least one of pins /CE1, CE2, /WE should be inactivated.

2. Do not input data to the I/O pins while they are in the output state.

Remark Write operation is done during the overlap time of a low level /CE1, /WE and a high level CE2.

Write Cycle Timing Chart 3 (CE2 Controlled)



Cautions 1. During address transition, at least one of pins /CE1, CE2, /WE should be inactivated.

2. Do not input data to the I/O pins while they are in the output state.

Remark Write operation is done during the overlap time of a low level /CE1, /WE and a high level CE2.



Low Vcc Data Retention Characteristics (TA = -25 to +85 °C)

Parameter	Symbol	Test Condition	μPD431000A-xxX		-xxX	Unit
			μPD431000A-AxxX		AxxX	
			μPD431000A-BxxX			
			MIN.	TYP.	MAX.	
Data retention supply voltage	Vccdr1	/CE1 ≥ Vcc − 0.2 V, CE2 ≥ Vcc − 0.2 V	2.0		5.5	V
	Vccdr2	CE2 ≤ 0.2 V	2.0		5.5	
Data retention supply current	ICCDR1	Vcc = 3.0 V, /CE1 ≥ Vcc − 0.2 V, CE2 ≥ Vcc − 0.2 V		0.5	20 Note	μΑ
	ICCDR2	Vcc = 3.0 V, CE2 ≤ 0.2 V		0.5	20 Note	
Chip deselection	tcdr		0			ns
to data retention mode						
Operation recovery time	t R		5			ms

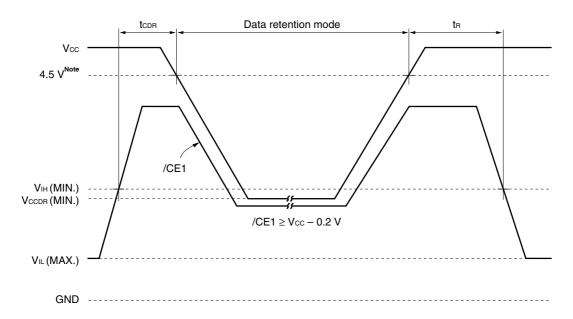
Note 2.5 μ A (Ta \leq 40 $^{\circ}$ C)

Data Sheet M10430EJAV0DS 15



Data Retention Timing Chart

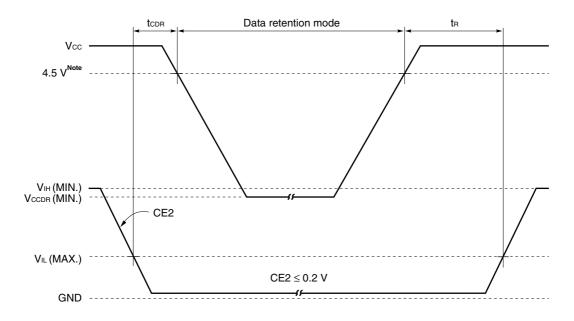
(1) /CE1 Controlled



Note A version: 3.0 V, B version: 2.7 V

Remark On the data retention mode by controlling /CE1, the input level of CE2 must be CE2 \geq Vcc - 0.2 V or CE2 \leq 0.2 V. The other pins (Address, I/O, /WE, /OE) can be in high impedance state.

(2) CE2 Controlled

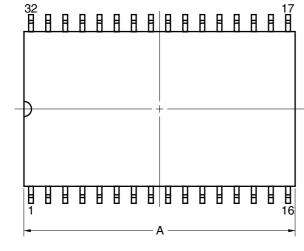


Note A version: 3.0 V, B version: 2.7 V

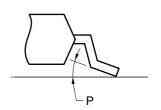
Remark On the data retention mode by controlling CE2, the other pins (/CE1, Address, I/O, /WE, /OE) can be in high impedance state.

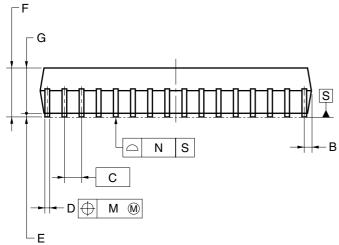
Package Drawings

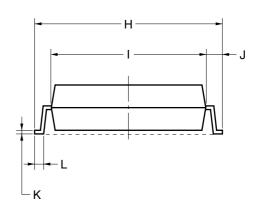
32-PIN PLASTIC SOP (13.34 mm (525))



detail of lead end







NOTE

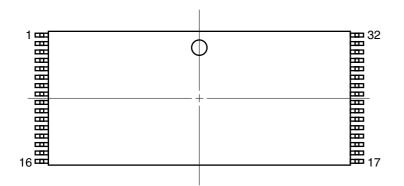
Each lead centerline is located within 0.12 mm of its true position (T.P.) at maximum material condition.

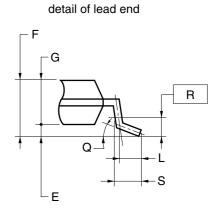
ITEM	MILLIMETERS
Α	20.61 MAX.
В	0.78 MAX.
С	1.27 (T.P.)
D	$0.40^{+0.10}_{-0.05}$
Е	0.15±0.05
F	2.95 MAX.
G	2.7
Н	14.1±0.3
I	11.3
J	1.4±0.2
K	$0.20^{+0.10}_{-0.05}$
L	0.8±0.2
М	0.12
N	0.10
Р	3°+7° -3°

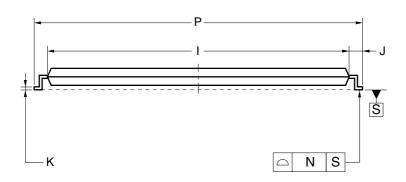
P32GW-50-525A-1

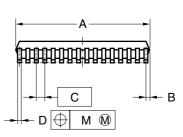


32-PIN PLASTIC TSOP(I) (8x20)









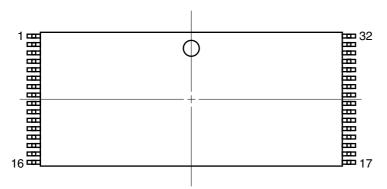
NOTES

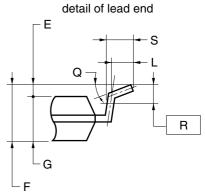
- Each lead centerline is located within 0.10 mm of its true position (T.P.) at maximum material condition.
- 2. "A" excludes mold flash. (Includes mold flash: 8.3 mm MAX.)

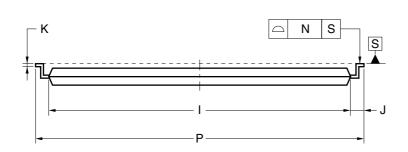
ITEM	MILLIMETERS
Α	8.0±0.1
В	0.45 MAX.
С	0.5 (T.P.)
D	0.22±0.05
Е	0.1±0.05
F	1.2 MAX.
G	0.97±0.08
- 1	18.4±0.1
J	0.8±0.2
K	0.145±0.05
L	0.5
М	0.10
N	0.10
Р	20.0±0.2
Q	3°+5°
R	0.25
S	0.60±0.15

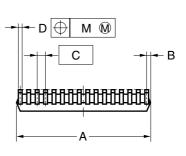
S32GZ-50-KJH1-2

32-PIN PLASTIC TSOP(I) (8x20)









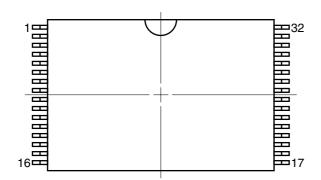
NOTES

- 1. Each lead centerline is located within 0.10 mm of its true position (T.P.) at maximum material condition.
- 2. "A" excludes mold flash. (Includes mold flash: 8.3 mm MAX.)

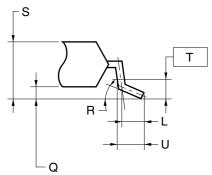
ITEM	MILLIMETERS
Α	8.0±0.1
В	0.45 MAX.
С	0.5 (T.P.)
D	0.22±0.05
E	0.1±0.05
F	1.2 MAX.
G	0.97±0.08
ı	18.4±0.1
J	0.8±0.2
K	0.145±0.05
L	0.5
М	0.10
N	0.10
Р	20.0±0.2
Q	3°+5° -3°
R	0.25
S	0.60±0.15
_	222C7 E0 KKH1 2

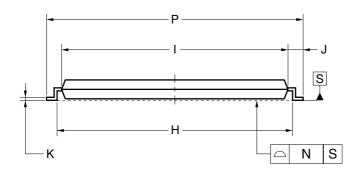
S32GZ-50-KKH1-2

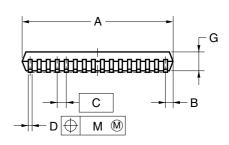
32-PIN PLASTIC TSOP(I) (8x13.4)











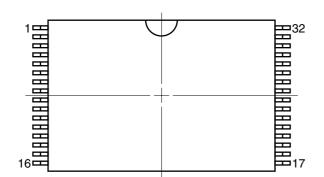
NOTES

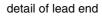
- Each lead centerline is located within 0.08 mm of its true position (T.P.) at maximum material condition.
- 2. "A" excludes mold flash. (Includes mold flash : 8.3 mm MAX.)

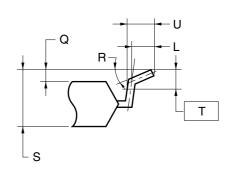
ITEM	MILLIMETERS
Α	8.0±0.1
В	0.45 MAX.
С	0.5 (T.P.)
D	0.22±0.05
G	1.0±0.05
Н	12.4±0.2
I	11.8±0.1
J	0.8±0.2
K	$0.145^{+0.025}_{-0.015}$
L	0.5
М	0.08
N	0.08
Р	13.4±0.2
Q	0.1±0.05
R	3°+5° -3°
S	1.2 MAX.
Т	0.25
U	0.6±0.15

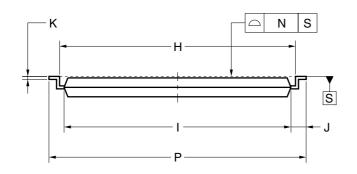
P32GU-50-9JH-2

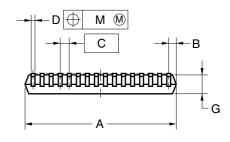
32-PIN PLASTIC TSOP(I) (8x13.4)











NOTES

- 1. Each lead centerline is located within 0.08 mm of its true position (T.P.) at maximum material condition.
- 2. "A" excludes mold flash. (Includes mold flash : 8.3 mm MAX.)

ITEM	MILLIMETERS
Α	8.0±0.1
В	0.45 MAX.
С	0.5 (T.P.)
D	0.22±0.05
G	1.0±0.05
Н	12.4±0.2
I	11.8±0.1
J	0.8±0.2
К	$0.145^{+0.025}_{-0.015}$
L	0.5
М	0.08
N	0.08
Р	13.4±0.2
Q	0.1±0.05
R	3°+5° -3°
S	1.2 MAX.
Т	0.25
U	0.6±0.15

P32GU-50-9KH-2



<R>

<R> <R>

<R> <R>

<R>

<R>

Recommended Soldering Conditions

Please consult with our sales offices for soldering conditions of the μ PD431000A-X.

Types of Surface Mount Device

μPD431000AGW-xxX : 32-pin PLASTIC SOP (13.34 mm (525)) μPD431000AGZ-xxX-KJH : 32-pin PLASTIC TSOP (I) (8×20) (Normal bent) μPD431000AGZ-xxX-KKH : 32-pin PLASTIC TSOP (I) (8×20) (Reverse bent) μPD431000AGZ-AxxX-KJH : 32-pin PLASTIC TSOP (I) (8×20) (Normal bent) μPD431000AGZ-AxxX-KKH : 32-pin PLASTIC TSOP (I) (8×20) (Reverse bent) μ PD431000AGZ-BxxX-KJH : 32-pin PLASTIC TSOP (I) (8×20) (Normal bent) μ PD431000AGU-BxxX-9JH : 32-pin PLASTIC TSOP (I) (8×13.4) (Normal bent) μPD431000AGU-BxxX-9KH : 32-pin PLASTIC TSOP (I) (8×13.4) (Reverse bent) : 32-pin PLASTIC SOP (13.34 mm (525)) μPD431000AGW-xxX-A μ PD431000AGZ-xxX-KJH-A : 32-pin PLASTIC TSOP (I) (8×20) (Normal bent) μPD431000AGZ-xxX-KKH-A : 32-pin PLASTIC TSOP (I) (8×20) (Reverse bent) μPD431000AGZ-AxxX-KJH-A: 32-pin PLASTIC TSOP (I) (8×20) (Normal bent) μPD431000AGZ-AxxX-KKH-A: 32-pin PLASTIC TSOP (I) (8×20) (Reverse bent) μPD431000AGZ-BxxX-KJH-A: 32-pin PLASTIC TSOP (I) (8×20) (Normal bent) <R> μPD431000AGU-BxxX-9JH-A: 32-pin PLASTIC TSOP (I) (8×13.4) (Normal bent) μPD431000AGU-BxxX-9KH-A: 32-pin PLASTIC TSOP (I) (8×13.4) (Reverse bent)



Revision History

Edition/	Page Ty		Type of	Location	Description
Date	This	Previous	revision		(Previous edition $ ightarrow$ This edition)
	edition	edition			
10th edition/	p.2	p.2	Addition	Ordering Information	Lead-free products have been added
Feb. 2006	pp.3-5	pp.3-5	Addition	Pin Configurations	Lead-free products have been added
	p.22	p.22	Addition	Recommended Soldering	Lead-free products have been added
				Conditions	

NEC μ PD431000A-X

[MEMO]

NEC μ PD431000A-X

[MEMO]

NEC μ PD431000A-X

[MEMO]



NOTES FOR CMOS DEVICES

(1) VOLTAGE APPLICATION WAVEFORM AT INPUT PIN

Waveform distortion due to input noise or a reflected wave may cause malfunction. If the input of the CMOS device stays in the area between $V_{\rm IL}$ (MAX) and $V_{\rm IH}$ (MIN) due to noise, etc., the device may malfunction. Take care to prevent chattering noise from entering the device when the input level is fixed, and also in the transition period when the input level passes through the area between $V_{\rm IL}$ (MAX) and $V_{\rm IH}$ (MIN).

(2) HANDLING OF UNUSED INPUT PINS

Unconnected CMOS device inputs can be cause of malfunction. If an input pin is unconnected, it is possible that an internal input level may be generated due to noise, etc., causing malfunction. CMOS devices behave differently than Bipolar or NMOS devices. Input levels of CMOS devices must be fixed high or low by using pull-up or pull-down circuitry. Each unused pin should be connected to VDD or GND via a resistor if there is a possibility that it will be an output pin. All handling related to unused pins must be judged separately for each device and according to related specifications governing the device.

③ PRECAUTION AGAINST ESD

A strong electric field, when exposed to a MOS device, can cause destruction of the gate oxide and ultimately degrade the device operation. Steps must be taken to stop generation of static electricity as much as possible, and quickly dissipate it when it has occurred. Environmental control must be adequate. When it is dry, a humidifier should be used. It is recommended to avoid using insulators that easily build up static electricity. Semiconductor devices must be stored and transported in an anti-static container, static shielding bag or conductive material. All test and measurement tools including work benches and floors should be grounded. The operator should be grounded using a wrist strap. Semiconductor devices must not be touched with bare hands. Similar precautions need to be taken for PW boards with mounted semiconductor devices.

4 STATUS BEFORE INITIALIZATION

Power-on does not necessarily define the initial status of a MOS device. Immediately after the power source is turned ON, devices with reset functions have not yet been initialized. Hence, power-on does not guarantee output pin levels, I/O settings or contents of registers. A device is not initialized until the reset signal is received. A reset operation must be executed immediately after power-on for devices with reset functions.

⑤ POWER ON/OFF SEQUENCE

In the case of a device that uses different power supplies for the internal operation and external interface, as a rule, switch on the external power supply after switching on the internal power supply. When switching the power supply off, as a rule, switch off the external power supply and then the internal power supply. Use of the reverse power on/off sequences may result in the application of an overvoltage to the internal elements of the device, causing malfunction and degradation of internal elements due to the passage of an abnormal current.

The correct power on/off sequence must be judged separately for each device and according to related specifications governing the device.

(6) INPUT OF SIGNAL DURING POWER OFF STATE

Do not input signals or an I/O pull-up power supply while the device is not powered. The current injection that results from input of such a signal or I/O pull-up power supply may cause malfunction and the abnormal current that passes in the device at this time may cause degradation of internal elements. Input of signals during the power off state must be judged separately for each device and according to related specifications governing the device.

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